Shashi

List of Publications by Year
in descending order

13	106	1478505	1474206
13 papers	**106** citations	**6** h-index	**9** g-index
13 all docs	**13** docs citations	**13** times ranked	**65** citing authors

#	Article	IF	Citations
1	Parameter Variation Analysis of Dopingless and Junctionless Nanotube MOSFET. Silicon, 2022, 14, 5255-5263.	3.3	4
2	Study and Analysis of Advanced 3D Multi-Gate Junctionless Transistors. Silicon, 2022, 14, 1053-1067.	3.3	9
3	Total Ionization Dose (TID) Effects on 2D MOS Devices. Transactions on Electrical and Electronic Materials, 2021, 22, 1-9.	1.9	4
4	Brace of Nanowire FETs in the Advancements and Miniaturizations of Recent Integrated Circuits Design. Advances in Computer and Electrical Engineering Book Series, 2021, , 139-170.	0.3	0
5	Hafnium based high-k dielectric gate-stacked (GS) gate material engineered (GME) junctionless nanotube MOSFET for digital applications. Applied Physics A: Materials Science and Processing, 2021, 127, 1.	2.3	6
6	Improved Sensitivity of Dielectric Modulated Junctionless Transistor for Nanoscale Biosensor Design. Sensor Letters, 2020, 18, 328-333.	0.4	8
7	Design and performance analysis of low-power SRAM based on electrostatically doped tunnel CNTFETs. Journal of Computational Electronics, 2019, 18, 856-863.	2.5	17
8	Design and simulation of nanoscale double-gate TFET/tunnel CNTFET. Journal of Semiconductors, 2018, 39, 044001.	3.7	18
9	Design and analysis of electrostatic doped tunnel CNTFET for various process parameters variation. Superlattices and Microstructures, 2018, 124, 160-167.	3.1	27
10	Electrostatically doped tunnel CNTFET model for low-power VLSI circuit design. Journal of Computational Electronics, 2018, 17, 1528-1535.	2.5	11
11	Comparative performance analysis of Carbon Nanotube and Si-Nanotube based Field effect Transistors. IOP Conference Series: Materials Science and Engineering, 0, 1033, 012028.	0.6	0
12	Analytical Modelling and Simulation Analysis of Junctionless Nanotube (JL NT) MOSFET. Transactions on Electrical and Electronic Materials, 0, , 1.	1.9	2
13	Silicon Material Based Tunnel FET for Controlling Ambipolar Current. Silicon, 0, , 1.	3.3	0